## Abstract of the Disclosure

A semiconductor laminating portion including a light emitting layer forming portion having at least an n-type layer and a p-type layer is formed on a semiconductor substrate. A current blocking layer is partially formed on its surface while a current diffusing electrode is formed on the entire surface thereof. A bonding electrode is formed thereon. The semiconductor laminating portion and the current diffusing electrode are separated into a plurality of light emitting unit portions (A), electrode pad portion B, and connecting portions C for connecting between the electrode pad portion B and the light emitting unit portions A or between two of the light emitting unit portions (A), and the semiconductor laminating portion between the respective light emitting unit portions A is removed through etching to make clearances except for the connecting portions C. The bonding electrode is formed on the electrode pad portion (B) which is formed so as to make the light emitting layer forming portion nonluminous. It is consequently possible to obtain a semiconductor light emitting device in which light emitted at the light emitting forming portion can be effectively extracted to the exterior, thereby improving the luminance with respect to input.